

KNOX SEMICONDUCTOR, INC.

A unique manufacturing process allows Knox Semiconductor to supply a range of Very Low Voltage Diodes having the lowest reverse leakage currents and low impedance at currents specified at 10 mA and below. These devices will find use in applications where conservation of battery life is a primary concern.

LOW LEVEL ZENER DIODES VERY LOW VOLTAGE, LOW LEAKAGE K120 - K510

TYPE NUMBER	NOMINAL ZENER VOLTAGE Vz @ Iz = 10 mA (Vdc)	DYNAMIC IMPEDANCE		REVERSE CURRENT @ 25° C	
		MAX Zz @ Iz = 10 mA (OHMS)	MAX Zzk @ Iz = 1 mA (OHMS)	MAX Ir (μA)	Vr (Vdc)
K120	1.2	17	100	.05	0.4
K150	1.5	17	100	.05	0.5
K180	1.8	20	125	.05	0.6
K210	2.1	17	100	.05	0.9
K240	2.4	17	100	.05	1.2
K270	2.7	17	100	.05	1.7
K300	3.0	17	100	.05	1.9
K330	3.3	17	100	.05	2.2
K360	3.6	17	100	.05	2.5
K390	3.9	17	100	.05	2.7
K430	4.3	23	135	.05	3.1
K470	4.7	23	135	.05	3.5
K510	5.1	23	135	.05	3.7
Package Style DC Power Dissipation Operating Temperature (Topr) Storage Temperature (Tstg) Voltage Tolerance: @ Ta = 50° C Standard Device DO-7 250 mW -65 to + 175° C -65 to + 200° C ±10%					